

LMK5Cxxxxx/LMK5Bxxxxx Programming

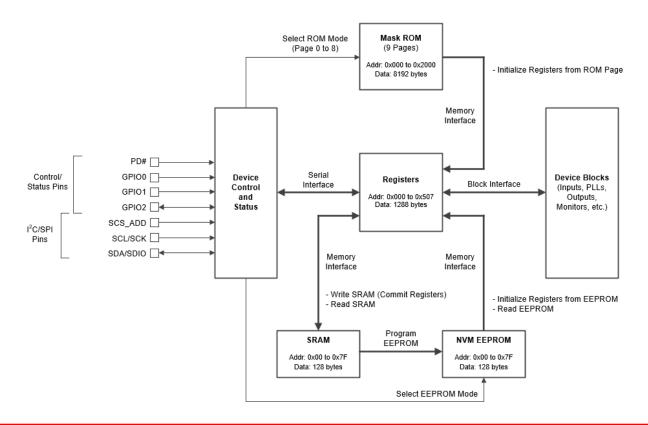
Nov 3 2023

Clocks and Timing Solutions

Revision History

Date	Description
2022-09-23	Initial release
2022-11-29	Updated to poll or delay before setting NVMUNLK = 0 after starting programming. Added notes on ROM page selection and outputs
2023-01-03	Generalized title for LMK5Cxxxxx and LMK5Bxxxxx
2023-05-17	Added Memory Overview
2023-08-11	Updated SRAWEEPROM address: 0x00 to 0x7F (128 bytes) Updated register address in Dec and Hex Updated RAMDAT register Updated direct write method steps Added LMK5C ROM page
2023-11-03	Added in-system programming section, changed title

Memory Overview



Part Identification

	Prototype (never released to ti.com)	Released to ti.com			
Date	Jan 2022	July 2022			
Top Marking	PK5B33216	K5B33216			
PRODID, R2	65 (0x41)	65 (0x41)			
REVID, R3	0	1			
PARTID, R4-R9	Unique t	o every part			
NVMCNT, R16	1 + number of EEPROM programming cycles made by user				
EEREV	Set by user when programming EEF	PROM using SRAM direct write method			

NVMCNT, R16

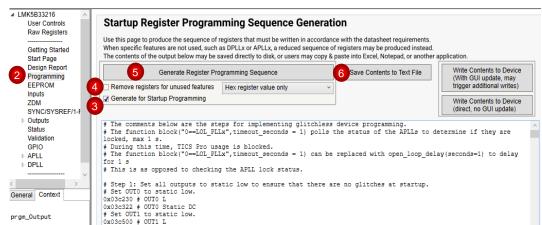
- NVMCNT is the number of successful EEPROM programming cycles.
- All LMK5Bxxxxx parts from <u>ti.com</u> start with NVMCNT = 1 because they are preprogrammed with the default EEPROM configuration.
 - Default EEPROM contains the APLL and output driver settings from ROM0.

GPIO2 at POR	GPIO0 at POR	ROM page with EE_ROM_PAGE_SEL = 0
L	L	ROM page 0. XO= 48 MHz, REFCLK = 25MHz, outputs 25 MHz, 100 MHz, 155.52 MHz, 156.25 MHz, 161.128125 MHz, 312.5MHz.

 If NVMCNT > 1, then the user has modified the EEPROM beyond factory setting.

Start-up Recommendations

- Open TICSPRO and load your desired .tcs settings.
- 2. Navigate to the "Programming" page.
- 3. Check the "Generate for Startup Programming" box.
- 4. (Optional) Check the "Remove registers for unused features" box.
 - This will not list registers for unused settings. For example, if DPLL2 is unused, then DPLL2 disable register will be listed but DPLL2 loop filter registers will not be listed.
- 5. Hit "Generate Register Programming Sequence" button.
- 6. To get the instructions as a .txt, click "Save Contents to Text File".



Start-up CRC ERROR Debugging

- If NVMCRCERR is set (R171[5] = 1), then there was an error loading EEPROM contents onto the registers.
- At power-up, it is expected for NVMSCRC (R170) to equal NVMLCRC (R172).
- Debugging tips
 - Power cycle the board. Does the NVMCRCERR clear?
 - Reprogram the EEPROM ensuring the proper programming sequence is followed. Does the NVMCRCERR clear?

EEPROM Overlay

- If the field **ROM_PLUS_EE** = 1, then an EEPROM overlay is loaded and many fields controlling APLL and output clock configuration will be loaded from the EEPROM.
- Allows EEPROM configuration to load at POR.

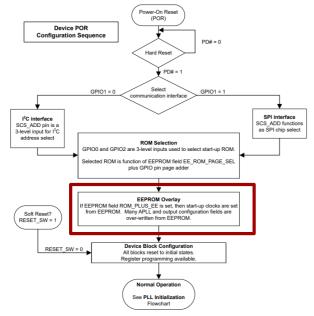


Figure 9-36. Device POR Configuration Sequence

EEPROM Programming Methods

- Two methods available:
 - REGCOMMIT (recommended)
 - Stores current configuration (all active registers) to EEPROM.
 - TICS Pro uses this method to program when you press **Program EEPROM** button

SRAM Direct Write

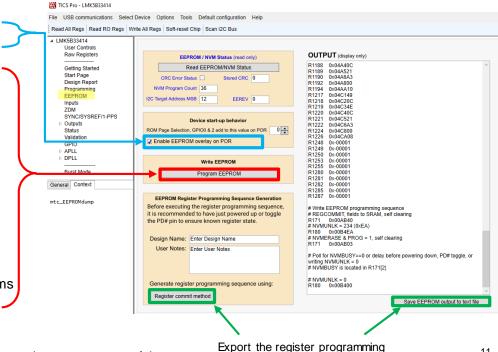
- Programs EEPROMone register/address at a time.
- Use if you want to do an in-system update without disrupting clocks. On next restart new config takes effect.
- Use to change the 5 MSBs of the I2C MSB address (TARGET_ADR_MSB) by writing to SRAM address 12.
- Use to change the EEPROM Revision Number (EEREV) by writing to SRAM address 13.
- Does require you to utilize the saved ".EPR" file.

EEPROM Programming: REGCOMMIT Method (recommended)

- Power cycle (toggle PD#)
- Program active registers and confirm the current configuration outputs as desired
- Enable EEPROM overlay
 - Set ROM PLUS EE (R20[7]) = 1 → R20 = 0x80
- Commit active registers to SRAM
 - Set REGCOMMIT (R171[6]) = 1 → R171 = 0x40 Note: REGCOMMIT is auto-cleared to 0 when transfer is completed
- Unlock EEPROM
 - Set NVMUNLK = 234 → R180[7:0] = 0xEA
- Erase EEPROM and initiate EEPROM programming
 - Set NVMERASE (R171[1]) = 1 \longrightarrow R171 = $\bar{0}$ x03
 - Set NVMPROG (R171[0]) = 1

Note: Step 5 & 6 must be atomic writes without any other register transactions in-between

- 7. Wait for EEPROM programming to finish
 - Poll NVMBUSY, R171[2], until cleared or wait ~ 500 ms
- Lock EEPROM
 - Set NVMUNLK = 0 → R180[7:0] = 0x00
- Power cycle and check outputs to confirm EEPROM programming was successful



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11

EEPROM Programming: SRAM Direct Write Method

- 1. Enable EEPROM overlay
- 2. Commit active registers to SRAM, set REGCOMMIT (R171[6]) = 1

 Note: REGCOMMIT is auto-cleared to 0 when transfer is completed

Write to SRAM

Program

EEPROM

- 3. Write the most significant five bits of the SRAM address to R173[4:0] (MEMADR_12:8).
- 4. Write the least significant eight bits of SRAM address to R174 (MEMADR).
- 5. Write the SRAM data byte to R176 (RAMDAT).
- 6. Repeat steps 3-5 for all desired SRAM values
- 7. Unlock EEPROM
- 8. Erase EEPROM and initiate EEPROM programming
 - Set NVMERASE (R171[1]) = 1
 - Set NVMPROG (R171[0]) = 1

Note: Step 7 & 8 must be atomic writes without any other register transactions in-between

- 9. Wait for EEPROM programming to finish
 - Poll NVMBUSY, R171[2], until cleared or wait ~ 500 ms
- 10. Lock EEPROM
 - Set NVMUNLK = 0

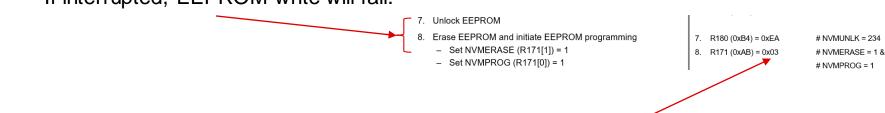
Example for updating the EEREV (R19) to value of 2:

- 1. R20 (0x14) = 0x80 # ROM_PLUS_EE = 1
- 2. R171 (0xAB) = 0x40 # REGCOMMIT = 1
- 3. R173 (0xAD) = 0x00 # EEREV addrH is 0x00
- 4. R174 (0xAE) = 0x0D # EEREV addrL is 0x0D
- 5. R176 (0xB0) = 0x02 # EEPROM Rev ID to 2
- 7. R180 (0xB4) = 0xEA # NVMUNLK = 234
- 8. R171 (0xAB) = 0x03 # NV MERASE = 1 &
 - # NVMPROG = 1
- 9. Poll NVMBUSY, R171[2], until cleared or wait ~ 500 ms
- 10. R180 (0xB4) = 0x00 # NVMUNLK = 0

12

Important Notes on EEPROM

- The I2C bus should not be interrupted (such as writing to another I2C address) in between NVMUNLK and NVMERASE/NVMPROG transactions.
 - If interrupted, EEPROM write will fail.



- NVMERASE and NVMPROG are atomic writes.
 - Ensure both are written in one register transaction.

R20 ROM_PLUS_EE and EE_ROM_PAGE_SEL

Use EEPROM overlay with ROM
R20 0x001480

ROM_PLUS_EE = 1 EE ROM PAGE SEL = 0

1.8 R20 Register (Offset = 0x14) [Reset = 0x0]

R20 is shown in Table 1-10.

Return to the Summary Table.

Note: Turn off EEPROM overlay by programming again using ROM_PLUS_EE = 0

Note: GPIO0, GPIO1, and EE_ROM_PAGE_SEL will select starting ROM page. ROM page will impact some clock output configuration pertaining to

which clocks are SYSREF. ROM8 allows any clock to startup as a non-Table 1-10. R20 Register Field Description seneral startup ROM.

Bit	Field	Туре	Reset	Description
7	ROM_PLUS_EE	R/W	0x0	When set, the thin EEPROM settings are loaded. This is user writeable to EEPROM only through SRAM register address 14. ROM=N, EEPROM=Y
6:3	EE_ROM_PAGE_SEL	R/W	0x0	EE_ROM_PAGE_SEL value is added to the GPIO pin value for selecting the start-up ROM. ROM=N, EEPROM=Y
2:0	RESERVED	R	0x0	Reserved

R171 REGCOMMIT

```
# Write EEPROM sequence
# REGCOMMIT, regs to SRAM, self clearing — R171 0x00AB40

1.95 .... Jx0]
```

R171 is shown in Table 1-97.

Table 1-97. R171 Register Field Descriptions

	<u> </u>					
Bit	Field	Туре	Reset	Description		
7	RESERVED	R	0x0	Reserved		
6	REGCOMMIT	R/WSC	0x0	Copy fields which also exist in SRAM to SRAM memory. The REGCOMMIT bit is automatically cleared to 0 when the transfer is complete. Next an EEPROM programming operation may be performed to update NVM EEPROM. When programming to alter an NVM profile, it is suggested to toggle PD# to assure default conditions, change the desired fields, then assert the REGCOMMIT bit. ROM=N, EEPROM=N		

R173 MEMADR_12:8

1.91 R173 Register (Offset = 0xAD) [Reset = 0x00]

Table 1-93. R173 Register Field Descriptions

Bit	Field	Туре	Reset	Description
7:5	RESERVED	R	0x0	Reserved
4:0	MEMADR_12:8	R/W	0x0	See Register 174

R174 MEMADR

1.92 R174 Register (Offset = 0xAE) [Reset = 0x00]

Table 1-94. R174 Register Field Descriptions

Bit	Field	Туре	Reset	Description
7:0	MEMADR	R/W	0x0	Memory Address. The MEMADR value determines the starting address for access to the on-chip memories. This same MEMADR value is used for EEPROM and SRAM access which share the same memory map and also ROM access. The NVMDAT field is used to read and write from EEPROM. The RAMDAT field is used to read and write from SRAM. The ROMDAT field is used to read and write from ROM.

R176 RAMDAT

1.93 R176 Register (Offset = 0xB0) [Reset = 0x00]

Table 1-95. R176 Register Field Descriptions

Bit	Field	Туре	Reset	Description
7:0	RAMDAT	R/W	0x0	RAM Read/Write Data. The first time an I2C/SMBus read or write transaction accesses the RAMDAT register address, either because it was explicitly targeted or because the address was auto-incremented, a read transaction will return the RAM data located at the address specified by the MEMADR register and a write transaction will cause the current I2C/SMBus data to be written to the address specified by the MEMADR register. Any additional accesses which are part of the same transaction will cause the RAM address to be incremented and a read or write access will take place to the next SRAM address. The I2C/SMBus address will no longer be auto-incremented (that is, the I2C/SMBus address will be locked to the RAMDAT register after the first access). Access to the RAMDAT register will terminate at the end of the current I2C/SMBus transaction.

R180 NVMUNLK

1.99 R180 Register (Offset = 0xB4) [Reset = 0x0]

R180 is shown in Table 1-101.

Return to the Summary Table.

Table 1-101. R180 Register Field Descriptions

Bit	Field	Туре	Reset	Description
7:0	NVMUNLK	R/W	0x0	NVM Prog Unlock. The NVMUNLK register must be written immediately prior to setting the NVMERASE and NVMPROG bit, otherwise the Erase/Program cycle will not be triggered. NVMUNLK must be written with a value of 0xEA. ROM=N, EEPROM=N

R171 NVMERASE and NVMPROG

NVMERASE & PROG = 1, self clearing #R171 0x00AB43

REGCOMMIT = 1

NVMERASE = 1

NVMPROG = 1

Table 1-97. R171 Register Field Descriptions (continued)

Bit	Field	Туре	Reset	Description
5	NVMCRCERR	R	0x0	NVM CRC Error Indication. The NVMCRCERR bit is set to 1 if a CRC Error has been detected when reading back from on-chip EEPROM during device configuration. ROM=N, EEPROM=N
4	RESERVED	R	0x0	Reserved
3	RESERVED	R	0x0	Reserved
2	NVMBUSY	R	0x0	NVM Program Busy Indication. The NVMBUSY bit is 1 during an on- chip EEPROM Erase/Program cycle. While NVMBUSY is 1 the on- chip EEPROM cannot be accessed. Toggling PD# or removing power while NVMBUSY is asserted will corrupt the EEPROM. ROM=N, EEPROM=N
1	NVMERASE	R/WSC	0x0	NVM Erase Start. The NVMERASE bit is used to begin an on-chip EEPROM Erase cycle. The Erase cycle is only initiated if the immediately preceding I2C/SMBus transaction was a write to the NVMUNLK register withthe appropriate code. The NVMERASE bit is automatically cleared to 0.
0	NVMPROG	R/WSC	0x0	NVM Program Start. The NVMPROG bit is used to begin an on-chip EEPROM Program cycle. The Program cycle is only initiated if the immediately preceding I2C/SMBus transaction was a write to the NVMUNLK register withthe appropriate code. The NVMPROG bit is automatically cleared to 0.

R180 NVMUNLK

1.99 R180 Register (Offset = 0xB4) [Reset = 0x0]

R180 is shown in Table 1-101.

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Table 1-101. R180 Register Field Descriptions

Bit	Field	Туре	Reset	Description
7:0	NVMUNLK	R/W	0x0	NVM Prog Unlock. The NVMUNLK register must be written immediately prior to setting the NVMERASE and NVMPROG bit, otherwise the Erase/Program cycle will not be triggered. NVMUNLK must be written with a value of 0xEA. ROM=N, EEPROM=N

LMK5C ROM page

Table 9-6. ROM page selection

GPIO2 ROM_ADD[1]		ROM page with EE_ROM_PAGE_SEL = 0
Н	Н	Low power mode. All PLLs off, all outputs off.
Н	М	IN1 = 10 MHz SE 50- Ω termination, XO = 38.88 MHz. All outputs = 100 MHz LVDS from DPLL1 (OUT0 to 3, 14, 15) and DPLL2 (OUT4 to 13).
L	L	IN1 = 10 MHz CMOS, XO = 38.88 MHz, OUT2 = 125 MHz HSDS, OUT3 = 156.25 MHz LVDS, OUT10 = 122.88 MHz LVDS.

LMK5B ROM page

Table 8-5. ROM Page Selection

GPIO2 at POR	GPIO0 at POR	ROM page with EE_ROM_PAGE_SEL = 0
L	L	ROM page 0. XO= 48 MHz, REFCLK = 25MHz, outputs 25 MHz, 100 MHz, 155.52 MHz, 156.25 MHz, 161.128125 MHz, 312.5MHz.
L	Н	ROM page 1. XO = 48MHz, outputs 25 MHz, 50 MHz, 100 MHz.
Н	L	ROM page 2. XO= 48 MHz, REFCLK = 25MHz, all outputs 156.25 MHz.
Н	Н	ROM page 3. Low power mode. All PLLs off, all outputs off.
L	М	ROM page 4. XO = 49.152 MHz, REFCLK = 19.44 MHz, outputs 100MHz, 312.5 MHz, 800 MHz.
М	L	ROM page 5. XO= 48 MHz, REFCLK = 156.25MHz, outputs 100 MHz, 125 MHz, 156.25 MHz
М	М	ROM page 6. XO= 48 MHz, REFCLK = 25MHz, all outputs 312.5 MHz.
М	Н	ROM page 7. XO= 48 MHz, REFCLK = 156.25MHz, outputs 100MHz, 125 MHz, 156.25 MHz.
Н	М	ROM page 8. XO= 48.008 MHz, REFCLK = 156.25MHz, outputs 25 MHz, 50 MHz, 100 MHz, 156.25 MHz